



STN4NF20L

N-channel 200 V, 1.1 Ω , 1 A SOT-223
low gate charge STripFET™ II Power MOSFET

Features

Order code	V _{DSS}	R _{DS(on)} max.	I _D
STN4NF20L	200 V	< 1.5 Ω	1 A

- 100% avalanche tested
- Low gate charge
- Exceptional dv/dt capability

Application

Switching applications

Description

This N-channel 200 V realized with STMicroelectronics unique STripFET™ process has specifically been designed to minimize input capacitance and gate charge. It is therefore suitable as primary switch in advanced high efficiency isolated DC-DC converters.

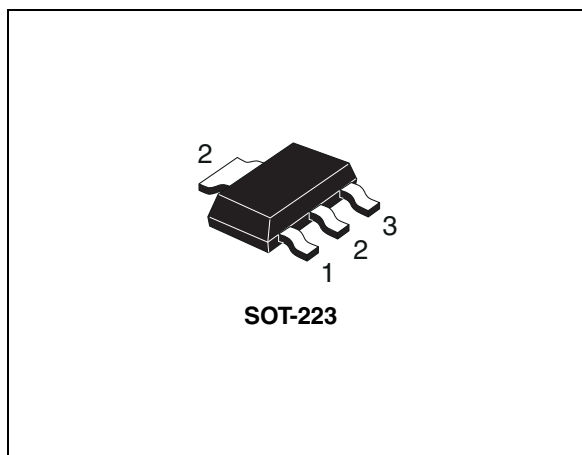


Figure 1. Internal schematic diagram

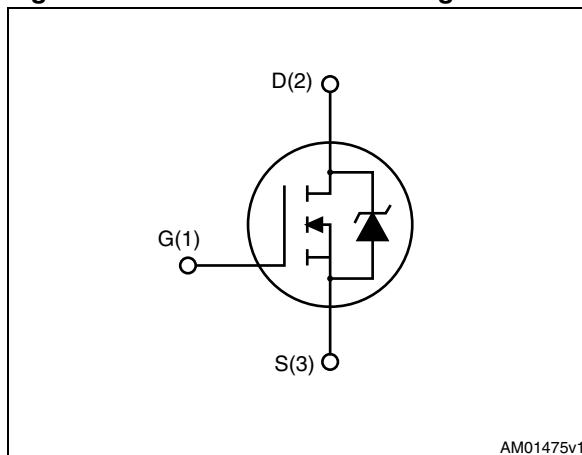


Table 1. Device summary

Order code	Marking	Package	Packaging
STN4NF20L	4NF20L	SOT-223	Tape and reel

Contents

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 20	V
I_D	Drain current continuous $T_C = 25\text{ }^\circ\text{C}$	1	A
I_D	Drain current continuous $T_C = 100\text{ }^\circ\text{C}$	0.63	A
$I_{DM}^{(1)}$	Drain current pulsed	4	A
$P_{TOT}^{(2)}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	3.3	W
$dv/dt^{(3)}$	Peak diode recovery voltage slope	20	V/ns
T_j T_{stg}	Operating junction temperature Storage temperature	- 55 to 150	$^\circ\text{C}$

1. Pulse width limited by safe operating area.
2. This value is rated according to $R_{thj-amb} \leq 10\text{ sec}$.
3. $I_{sd} \leq 1\text{ A}$, $di/dt \leq 200\text{ A}/\mu\text{s}$, $V_{DD} \leq 80\% V_{(BR)DSS}$.

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-amb}^{(1)}$	Thermal resistance junction to ambient	38	$^\circ\text{C}/\text{W}$
$R_{thj-amb}^{(2)}$		62.5	$^\circ\text{C}/\text{W}$

1. When mounted on 1 inch² FR-4 board, 2 oz. Cu, ($t < 10\text{ sec}$).
2. When mounted on 1 inch² FR-4 board, 2 oz. Cu, ($t > 10\text{ sec}$).

Table 4. Thermal data

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive ⁽¹⁾	1	A
E_{AS}	Single pulse avalanche energy ⁽²⁾	90	mJ

1. Pulse width limited by T_{JMAX} .
2. Starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$.

2 Electrical characteristics

(T_{case} = 25 °C unless otherwise specified)

Table 5. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	I _D = 1 mA, V _{GS} = 0	200			V
I _{DSS}	Zero gate voltage drain current (V _{GS} = 0)	V _{DS} = Max rating V _{DS} = Max rating, T _C =125 °C			1 50	μA μA
I _{GSS}	Gate-body leakage current (V _{DS} = 0)	V _{GS} = ± 20 V, V _{DS} =0			± 100	nA
V _{GS(th)}	Gate threshold voltage	V _{GS} = V _{DS} , I _D = 250 μA	1	2	3	V
R _{DS(on)}	Static drain-source on resistance	V _{GS} = 10 V, I _D = 0.5 A V _{GS} = 5 V, I _D = 0.5 A		1.1 1.13	1.5 1.55	Ω Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C _{iss}	Input capacitance	V _{DS} = 25 V, f = 1 MHz, V _{GS} = 0	-	150	-	pF
C _{oss}	Output capacitance			30		pF
C _{rss}	Reverse transfer capacitance			4		pF
R _g	Intrinsic gate resistance	f=1 MHz open drain	-	5.5	-	Ω
Q _g	Total gate charge	V _{DD} = 160 V, I _D = 1 A, V _{GS} = 10 V (see Figure 13)	-	0.9	-	nC
Q _{gs}	Gate-source charge			2.6		nC
Q _{gd}	Gate-drain charge			6.9		nC

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
t _{d(v)}	Voltage delay time	V _{DD} = 100 V, I _D = 0.5 A, R _G = 4.7 Ω, V _{GS} = 10 V (see Figure 12)	-	3.6	-	ns
t _r	Voltage rise time			2		ns
t _f	Current fall time			10.4		ns
t _{c(off)}	Crossing time			15.4		ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM}^{(1)}$	Source-drain current Source-drain current (pulsed)		-		1 4	A A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 1\text{ A}$, $V_{GS} = 0$	-		1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 1\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$ (see Figure 14)	-	51 90 3.5		ns nC A
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 1\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 14)	-	56 105 3.7		ns nC A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

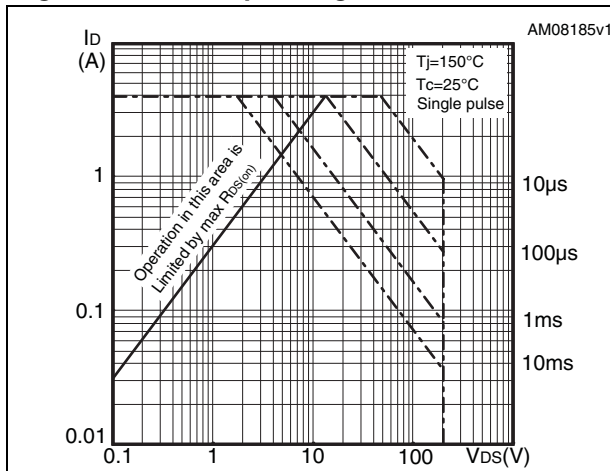


Figure 3. Thermal impedance

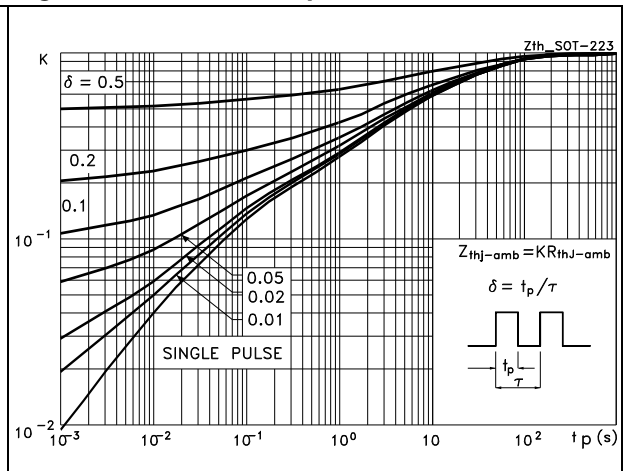


Figure 4. Output characteristics

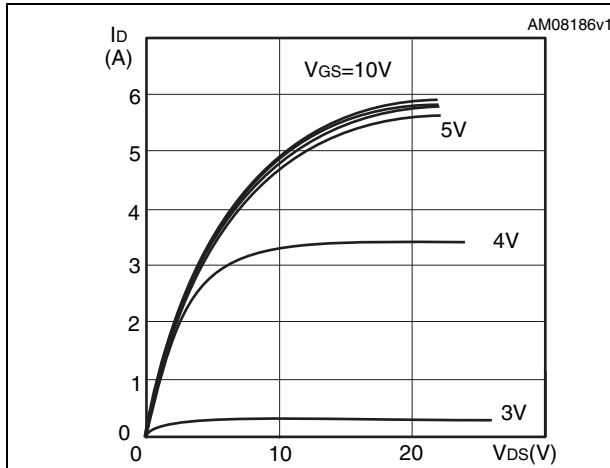


Figure 5. Transfer characteristics

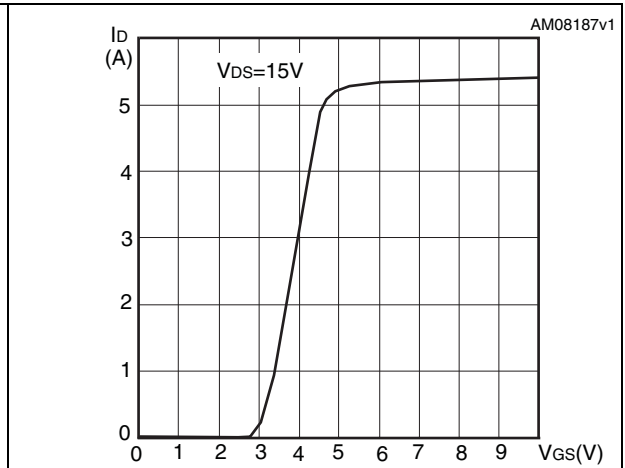


Figure 6. Normalized BV_{DSS} vs temperature

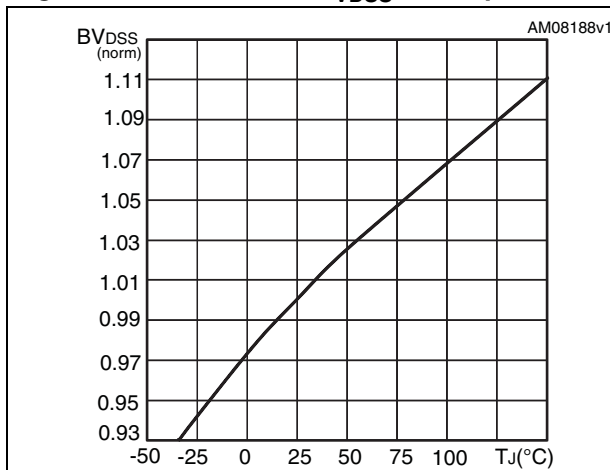


Figure 7. Static drain-source on resistance

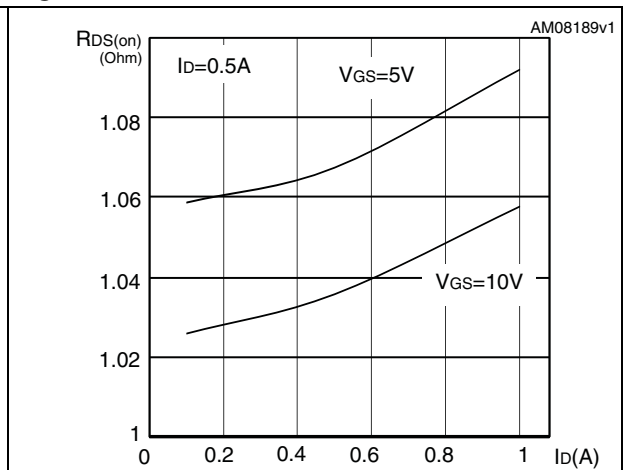


Figure 8. Gate charge vs gate-source voltage Figure 9. Capacitance variations

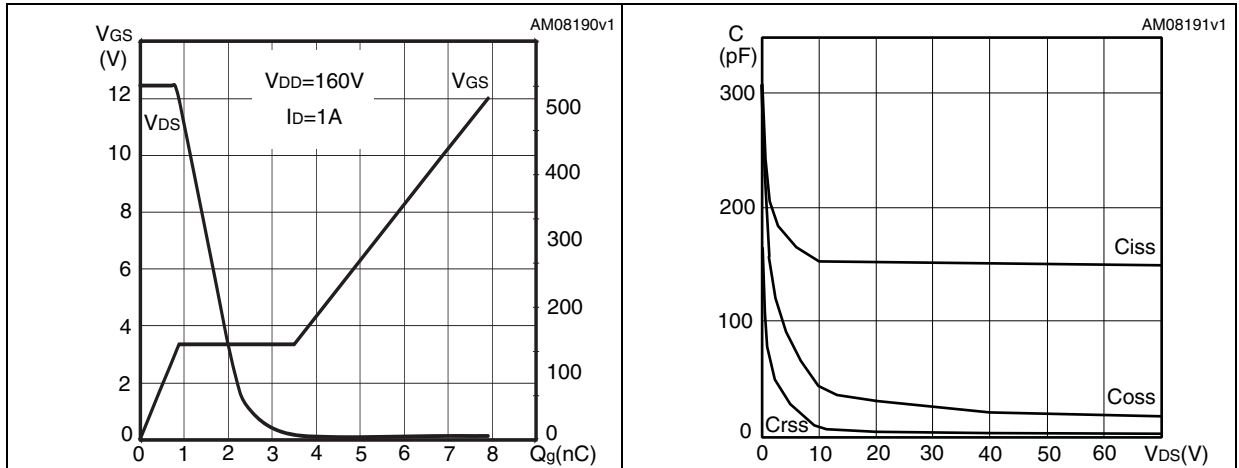
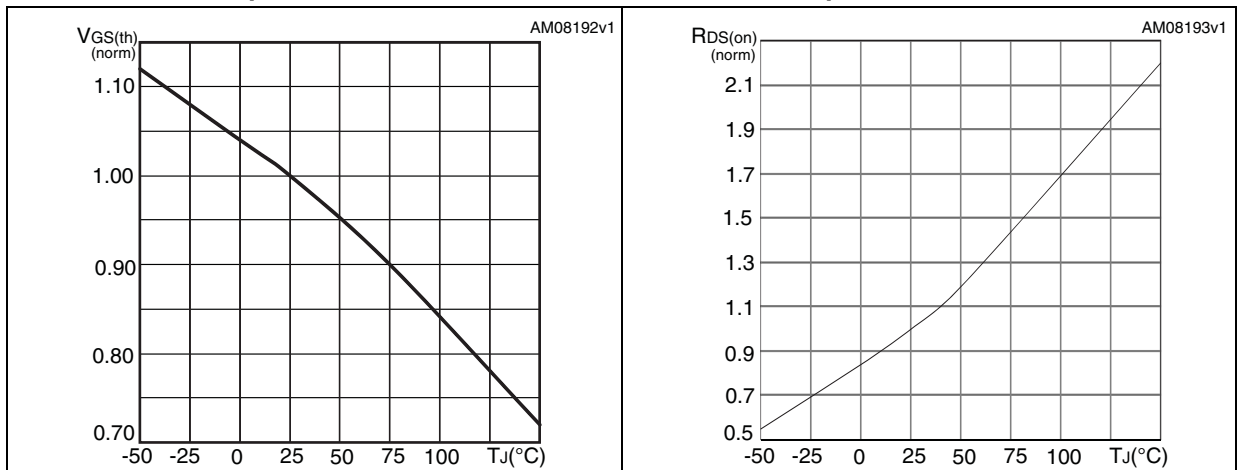
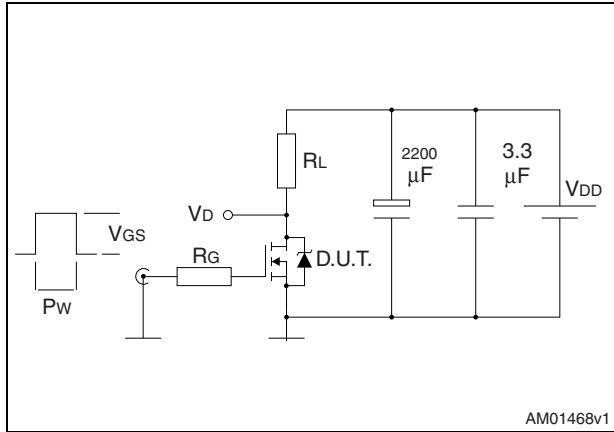


Figure 10. Normalized gate threshold voltage vs temperature Figure 11. Normalized on resistance vs temperature



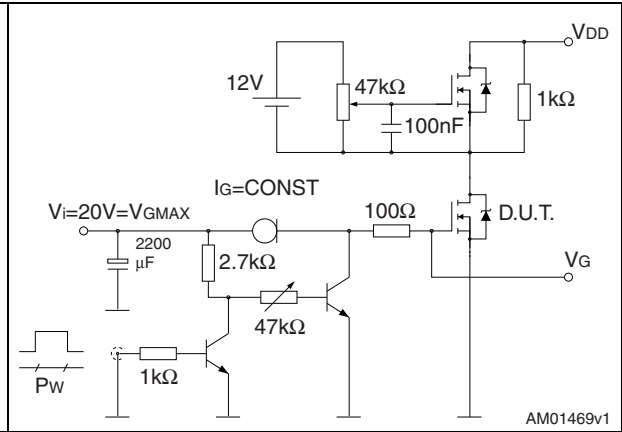
3 Test circuits

Figure 12. Switching times test circuit for resistive load



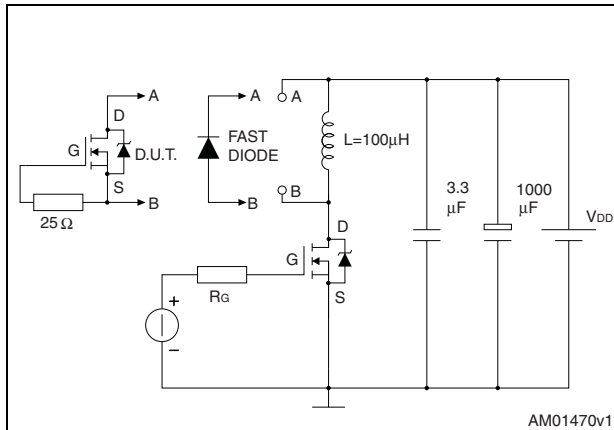
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Figure 13. Gate charge test circuit



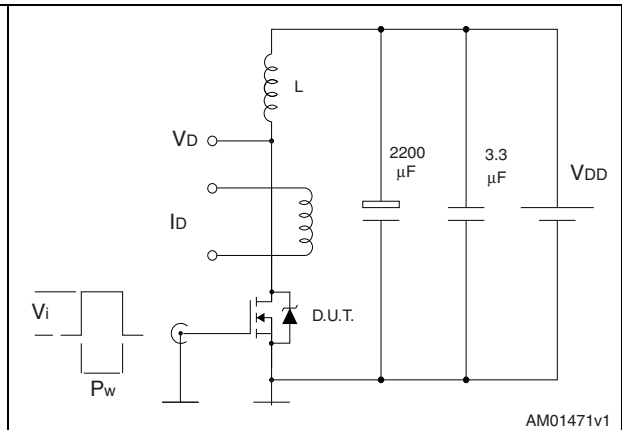
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Figure 14. Test circuit for inductive load switching and diode recovery times



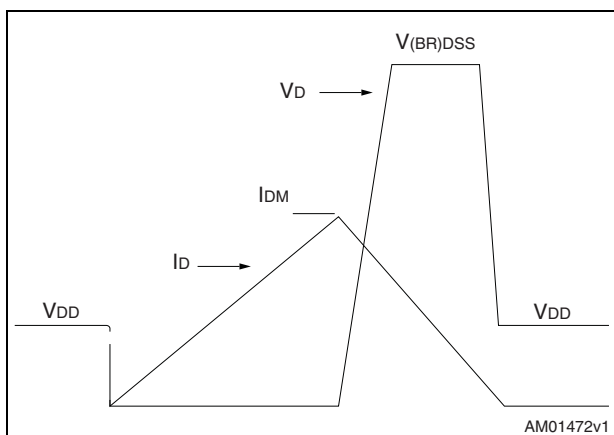
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Figure 15. Unclamped inductive load test circuit



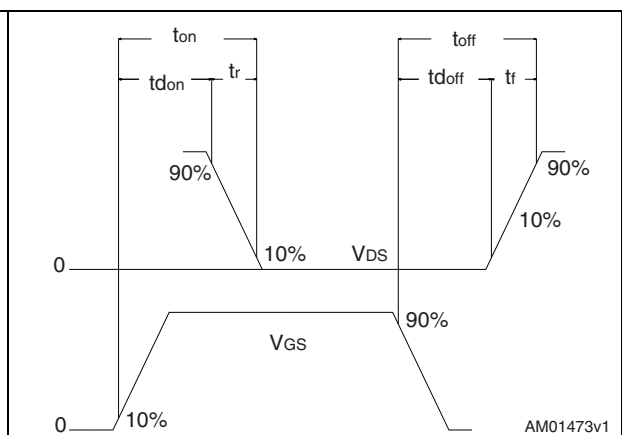
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Figure 16. Unclamped inductive waveform



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Figure 17. Switching time waveform



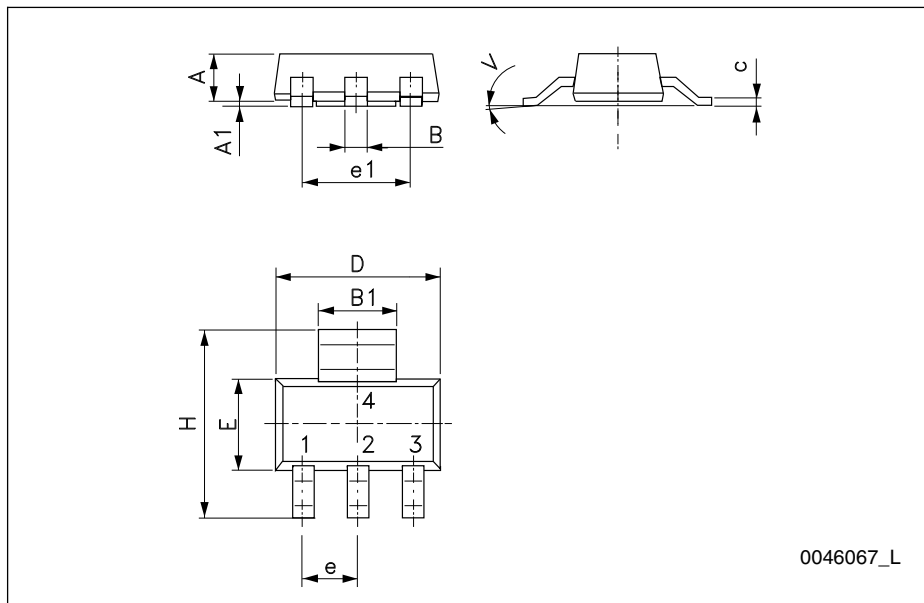
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4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

SOT-223 mechanical data

DIM.	mm.		
	min.	typ	max.
A			1.80
A1	0.02		0.1
B	0.60	0.70	0.85
B1	2.90	3.00	3.15
c	0.24	0.26	0.35
D	6.30	6.50	6.70
e		2.30	
e1		4.60	
E	3.30	3.50	3.70
H	6.70	7.00	7.30
V			10°



5 Revision history

Table 9. Document revision history

Date	Revision	Changes
29-Apr-2010	1	First release.
11-Oct-2010	2	Document status promoted from preliminary data to datasheet.

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